

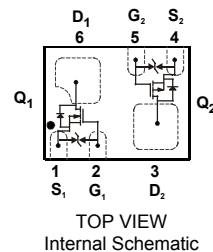
COMPLEMENTARY PAIR ENHANCEMENT MODE FIELD EFFECT TRANSISTOR
Features

- Low On-Resistance
- Low Gate Threshold Voltage $V_{GS(th)} < 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Complementary Pair MOSFET
- Ultra-Small Surface Mount Package
- **ESD Protected Gate**
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

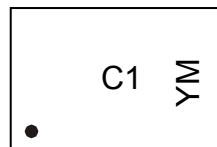
- Case: X1-DFN1612-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 (e4)
- Marking Information: See Page 6
- Ordering Information: See Page 6
- Weight: 0.003 grams (approximate)

X1-DFN1612-6


Ordering Information (Note 4)

Part Number	Case	Packaging
DMC2004LPK-7	X1-DFN1612-6	3000/Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information


C1 = Marking Code
 YM = Date Code Marking
 Y = Year (ex: Z = 2012)
 M = Month (ex: 9 = September)

Date Code Key

Year	2012	2013	2014	2015	2016	2017	2018
Code	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings N-CHANNEL – Q₁ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (Note 5)	I _D	750 540	mA
		T _A = +25°C T _A = +85°C	

Maximum Ratings P-CHANNEL – Q₂ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Drain Current (Note 5)	I _D	-600 -430	mA
		T _A = +25°C T _A = +85°C	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	500	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	250	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C

Electrical Characteristics N-CHANNEL – Q₁ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 10μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	± 1	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	1.0	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.4	0.55	Ω	V _{GS} = 4.5V, I _D = 540mA
		—	0.5	0.70		V _{GS} = 2.5V, I _D = 500mA
		—	0.7	0.90		V _{GS} = 1.8V, I _D = 350mA
Forward Transfer Admittance	Y _{fs}	200	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage (Note 6)	V _{SD}	0.5	—	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	150	pF	V _{DS} = 16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	

Electrical Characteristics P-CHANNEL – Q₂ (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	± 1.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.7	0.9	Ω	V _{GS} = -4.5V, I _D = -430mA
		—	1.1	1.4		V _{GS} = -2.5V, I _D = -300mA
		—	1.7	2.0		V _{GS} = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	200	—	—	mS	V _{DS} = 10V, I _D = 0.2A
Diode Forward Voltage (Note 5)	V _{SD}	-0.5	—	-1.2	V	V _{GS} = 0V, I _S = -115mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	—	175	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	—	30	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	20	pF	

Notes: 5. Device mounted on FR-4 PCB.
6. Short duration pulse test used to minimize self-heating effect.

Q₁, N-CHANNEL

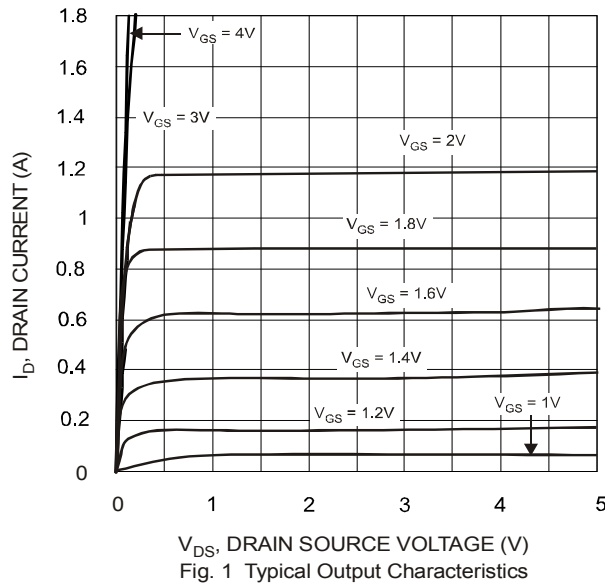


Fig. 1 Typical Output Characteristics

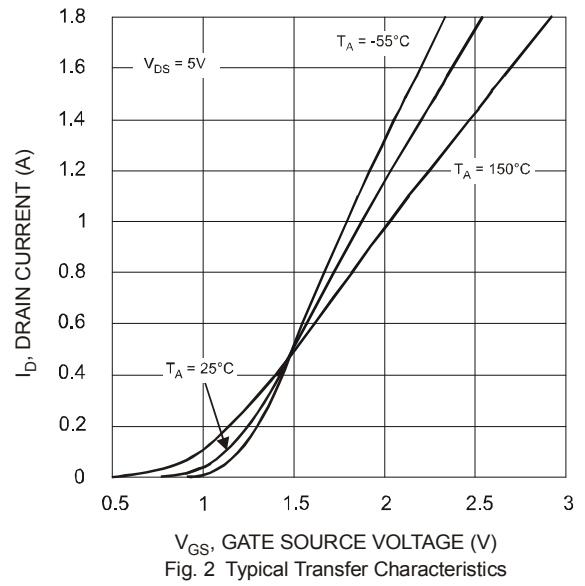


Fig. 2 Typical Transfer Characteristics

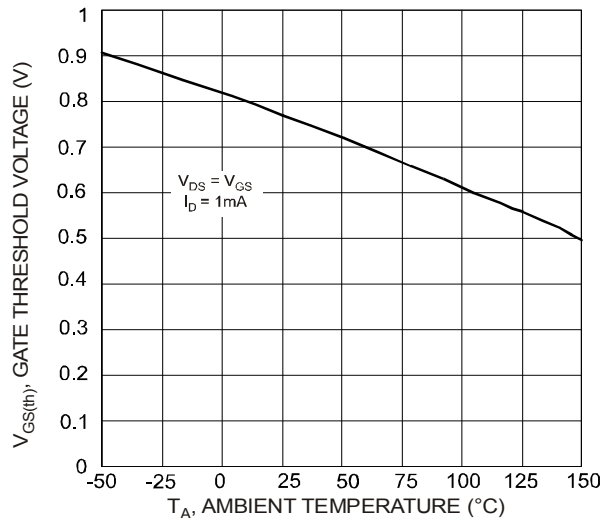


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

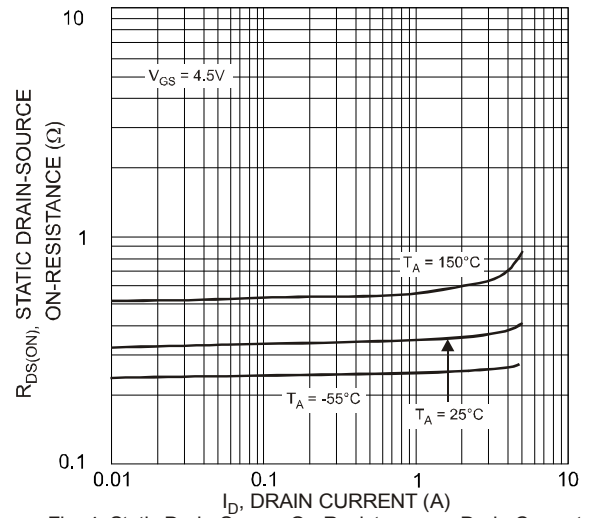


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

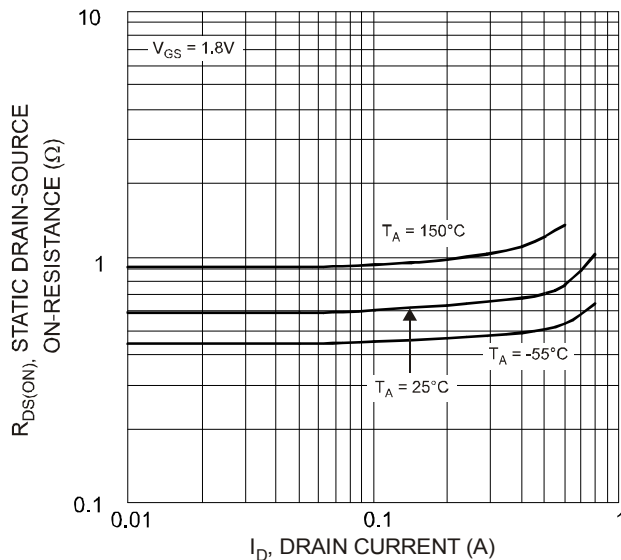


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

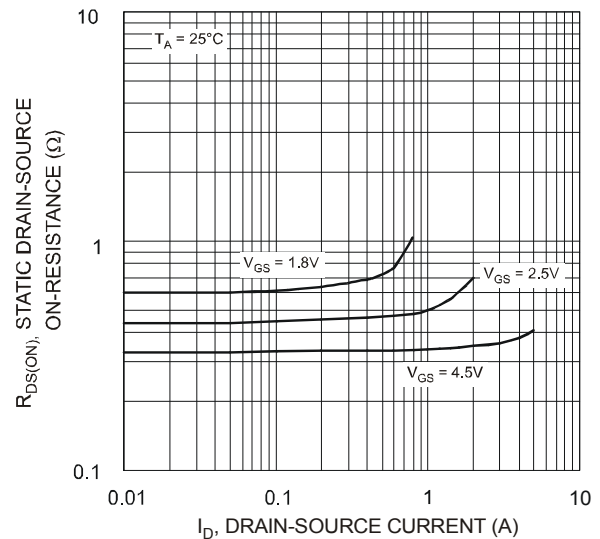


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

Q₁, N-CHANNEL, (cont.)

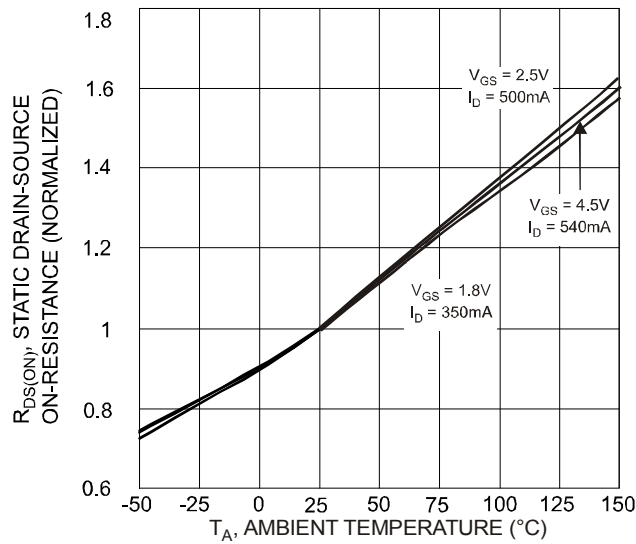


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

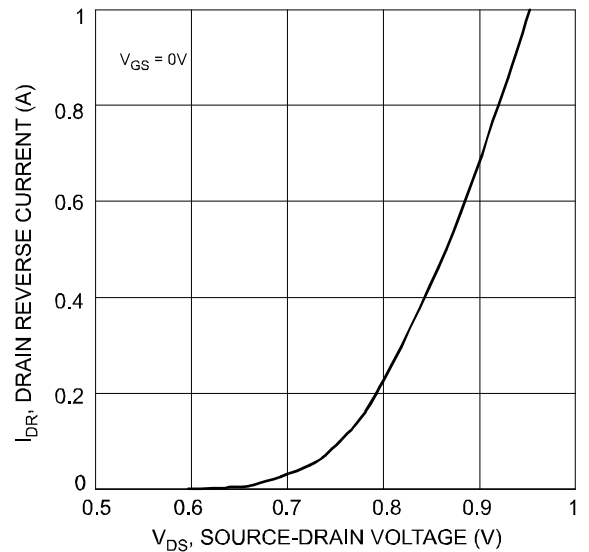


Fig. 8 Drain Reverse Current vs. Source-Drain Voltage

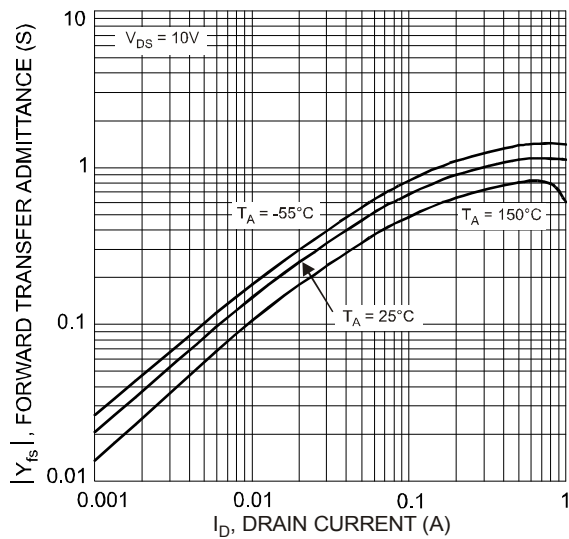


Fig. 9 Forward Transfer Admittance vs. Drain Current

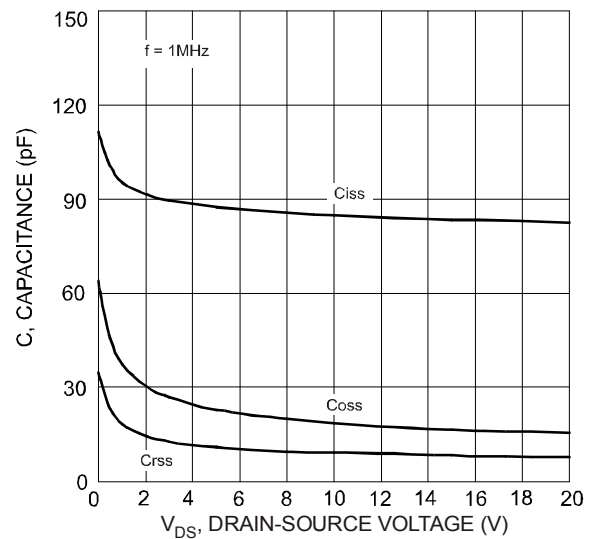


Fig. 10 Typical Capacitance

Q₂, P-CHANNEL

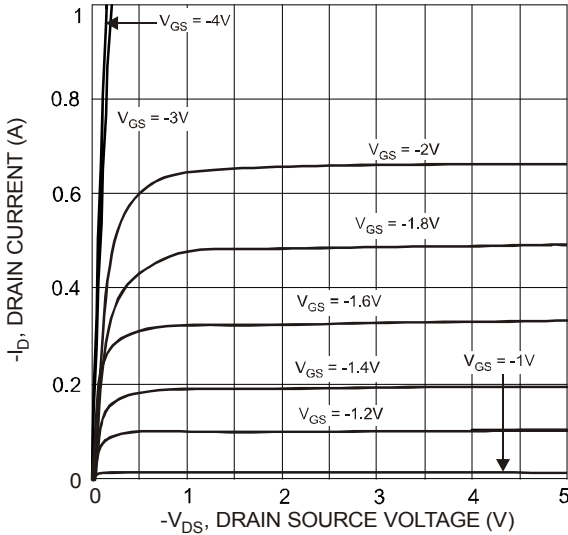


Fig. 11 Typical Output Characteristics

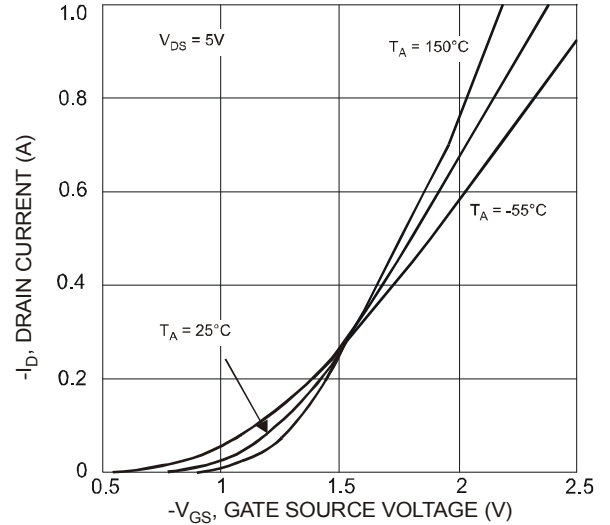


Fig. 12 Typical Transfer Characteristics

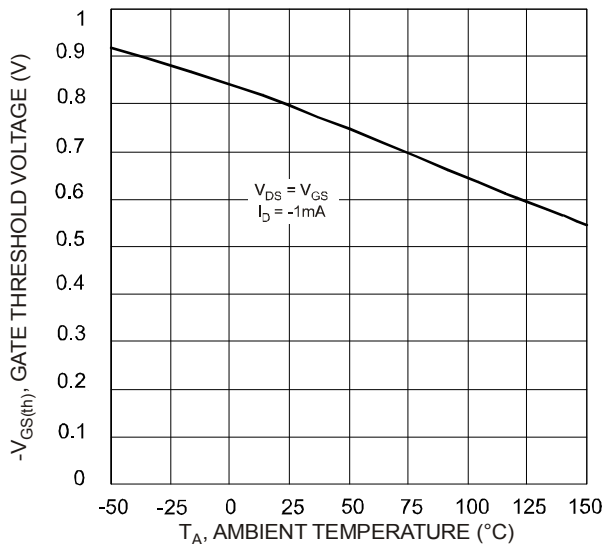


Fig. 13 Gate Threshold Voltage vs. Ambient Temperature

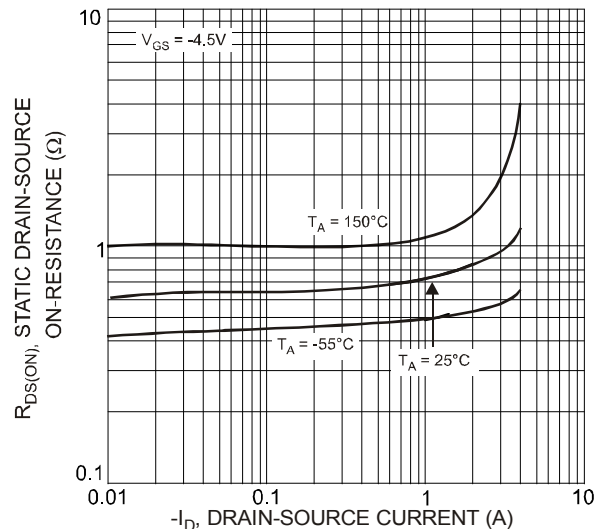


Fig. 14 Static Drain-Source On-Resistance vs. Drain Current

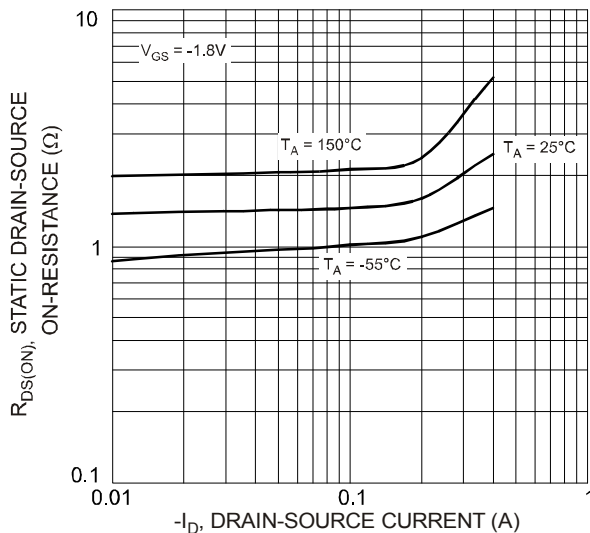


Fig. 15 Static Drain-Source On-Resistance vs. Drain Current

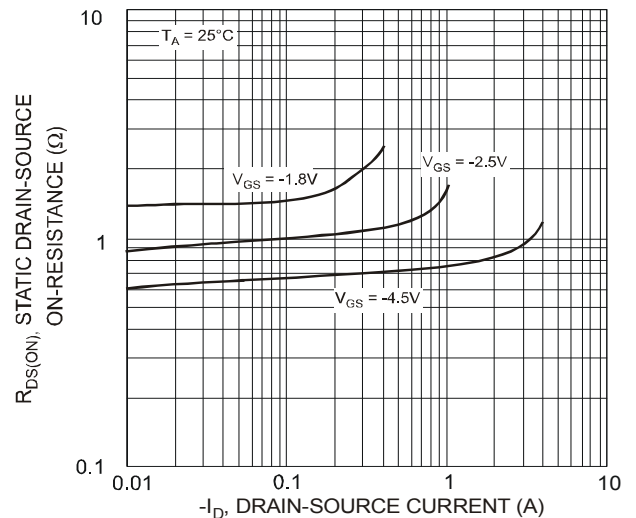


Fig. 16 Static Drain-Source On-Resistance vs. Drain-Source Current vs. Gate Source Voltage

Q₂, P-CHANNEL, (cont.)

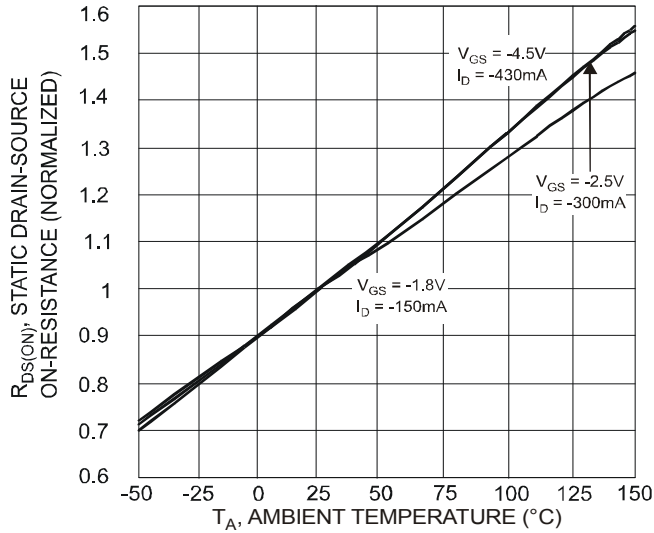


Fig. 17 Static Drain-Source On-State Resistance vs. Ambient Temperature

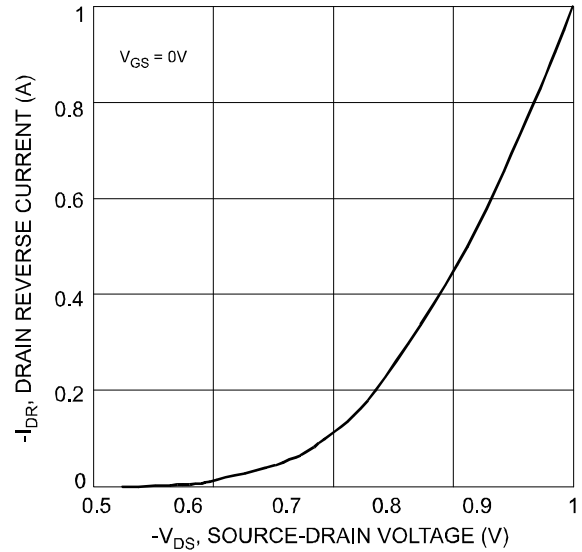


Fig. 18 Drain Reverse Current vs. Source-Drain Voltage

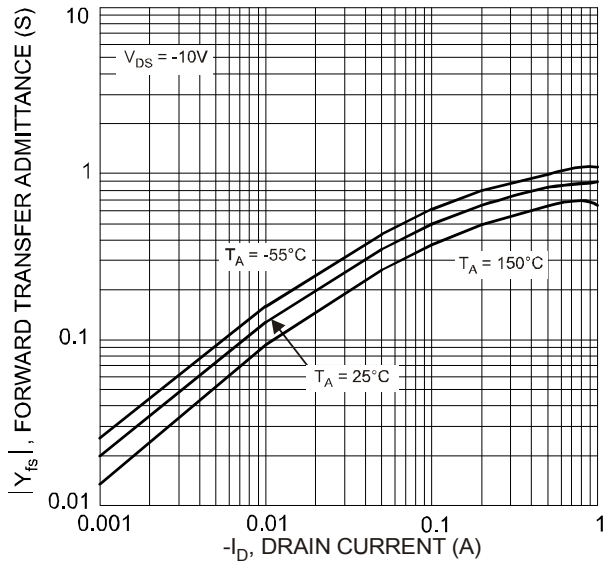


Fig. 19 Forward Transfer Admittance vs. Drain Current

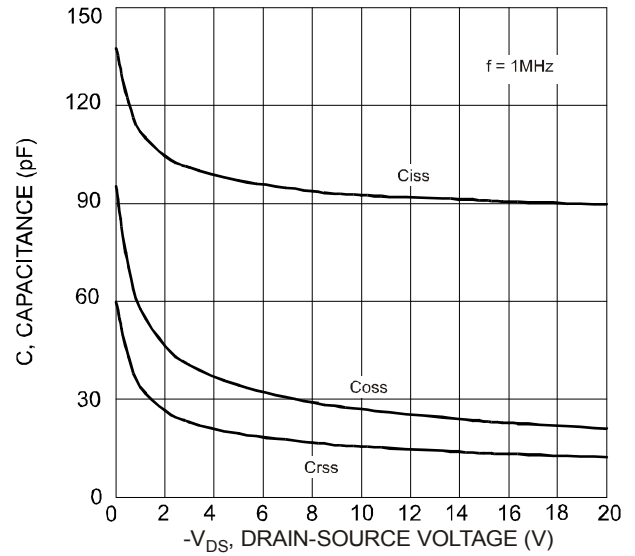
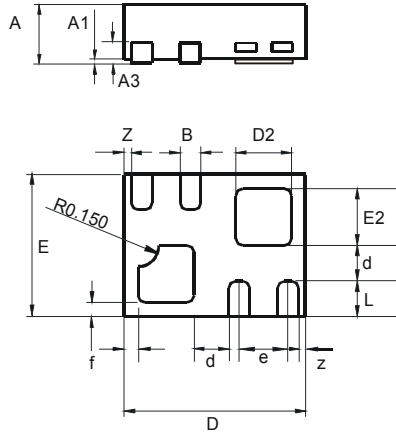


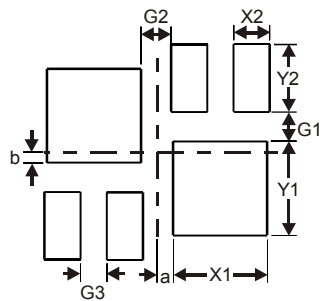
Fig. 20 Typical Capacitance

Package Outline Dimensions



X1-DFN1612-6			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.55	1.675	1.60
d	—	—	0.25
D2	0.40	0.60	0.50
E	1.15	1.28	1.20
e	—	—	0.40
E2	0.45	0.65	0.55
f	—	—	0.15
L	0.20	0.30	0.25
Z	—	—	0.10
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
G1	0.15
G2	0.175
G3	0.15
X1	0.60
X2	0.25
Y1	0.65
Y2	0.45
a	0.10
b	0.15

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